

## 1. General description

Planar passivated Silicon Controlled Rectifier with sensitive gate in a SOT54 (TO-92) plastic package. This SCR is designed to be interfaced directly to microcontrollers, logic ICs and other low power gate trigger circuits.

#### 2. Features and benefits

- · Guaranteed minimum gate trigger current limit
- · Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Direct triggering from low power gate circuits and logic ICs

## 3. Applications

- Ground Fault Interrupters (GFI)
- Leakage Current Circuit Breakers (LCCB)
- Residual Current Devices (RCD)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	500	V
$I_{T(AV)}$	average on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 1</u>	-	-	0.5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	0.8	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	-	8	Α
		half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 8.3 ms	-	-	9	Α
Tj	junction temperature		-	-	125	°C
Static charact	eristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 7	20	50	200	μΑ
Dynamic char	acteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 335 V; $T_j$ = 125 °C; $R_{GK}$ = 1 kΩ; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12	500	800	-	V/µs

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_{DM}$ = 335 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12	-	25	-	V/µs

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Α	anode		
2	G	gate		
3	K	cathode	TO-92 (SOT54)	

# 6. Ordering information

#### **Table 3. Ordering information**

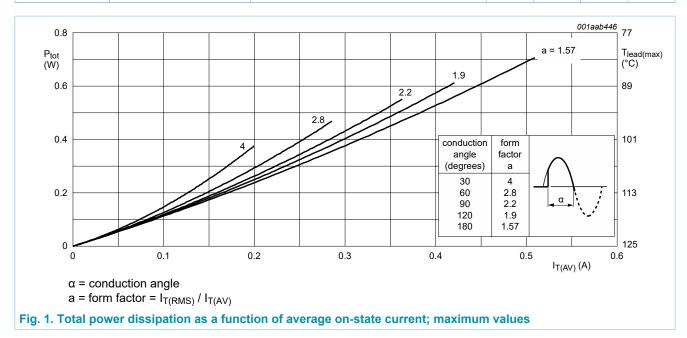
Type number	Package					
	Name	Description	Version			
BT168E	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

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# 7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	500	V
$V_{RRM}$	repetitive peak reverse voltage		-	500	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 1</u>	-	0.5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	8.0	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	8	А
		half sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 8.3 ms	-	9	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$t_p$ = 10 ms; SIN	-	0.32	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 2 \text{ A}$ ; $I_G = 10 \text{ mA}$ ; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	1	Α
$V_{RGM}$	peak reverse gate voltage		-	5	V
P <sub>GM</sub>	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C



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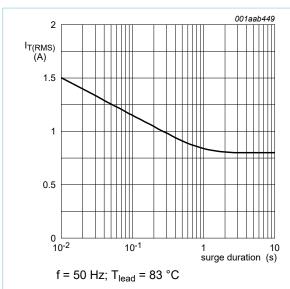


Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents

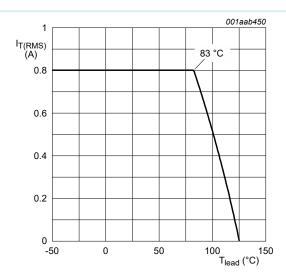


Fig. 3. RMS on-state current as a function of lead temperature; maximum values

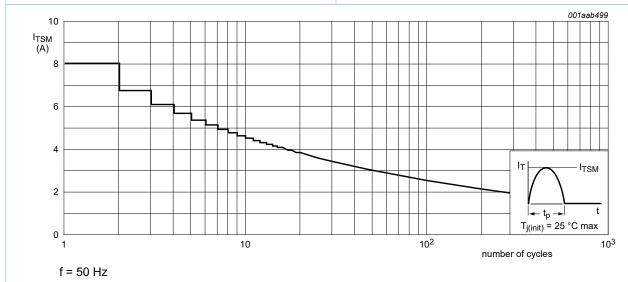
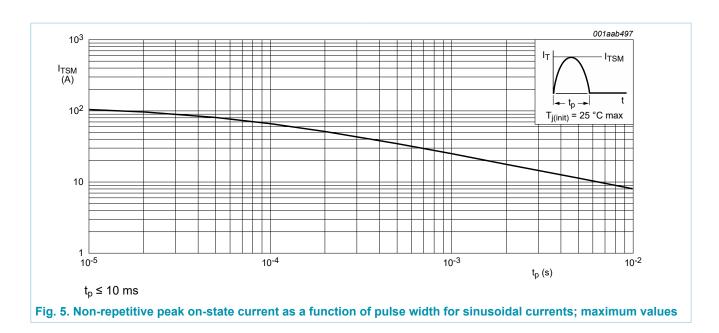


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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#### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	<u>Fig. 6</u>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

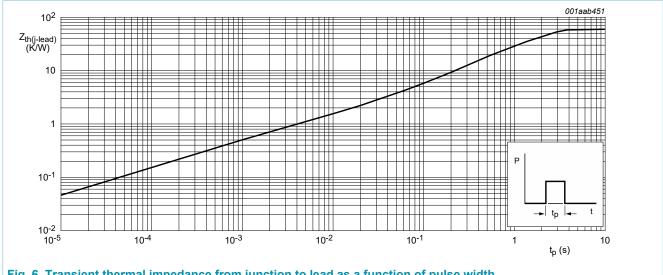


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

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## 9. Characteristics

#### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics				-	
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 7	20	50	200	μΑ
IL	latching current	$V_D$ = 12 V; $I_G$ = 10 mA; $T_j$ = 25 °C; $R_{GK(ext)}$ = 1 k $\Omega$ ; Fig. 8	-	2	6	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; R_{GK(ext)} = 1 \text{ k}\Omega;$ Fig. 9	-	2	5	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.2 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.25	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 11	-	0.5	0.8	V
		$V_D = 500 \text{ V}; I_T = 10 \text{ mA}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.2	0.3	-	V
I <sub>D</sub>	off-state current	$V_D = 500 \text{ V}; R_{GK(ext)} = 1 \text{ k}\Omega; T_j = 125 °C$	-	0.05	0.1	mA
I <sub>R</sub>	reverse current	$V_R = 500 \text{ V}; T_j = 125 \text{ °C}; R_{GK(ext)} = 1 \text{ k}\Omega$	-	0.05	0.1	mA
Dynamic cl	haracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 335 V; $T_j$ = 125 °C; $R_{GK}$ = 1 kΩ; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12	500	800	-	V/µs
		$V_{DM}$ = 335 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12	-	25	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 2 A; $V_D$ = 500 V; $I_G$ = 10 mA; $dI_G/dt$ = 0.1 A/ $\mu$ s; $T_j$ = 25 °C	-	2	-	μs
t <sub>q</sub>	commutated turn-off time	$V_{DM} = 335 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{TM} = 1.6 \text{ A}; V_R = 35 \text{ V}; (dI_T/dt)_M = 30 \text{ A/}\mu\text{s}; dV_D/dt = 2 \text{ V/}\mu\text{s}; R_{GK(ext)} = 1 \text{ k}\Omega; (V_{DM} = 67\% \text{ of V}_{DRM})$	-	100	-	μs

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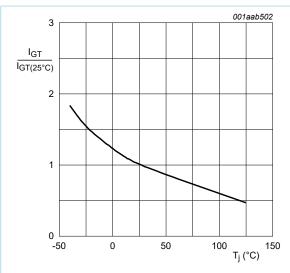


Fig. 7. Normalized gate trigger current as a function of junction temperature

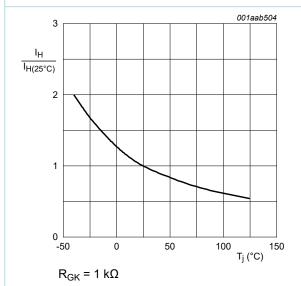


Fig. 9. Normalized holding current as a function of junction temperature

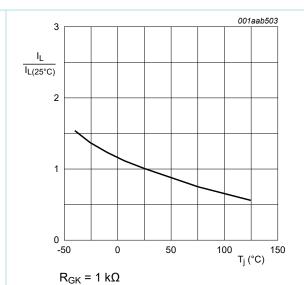
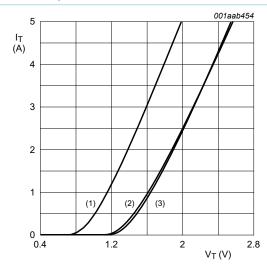


Fig. 8. Normalized latching current as a function of junction temperature



 $V_o$  = 1.067 V;  $R_s$  = 0.187  $\Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

(2) T<sub>j</sub> = 125 °C; maximum values (3) T<sub>j</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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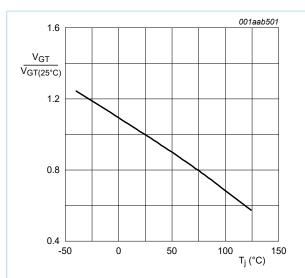


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

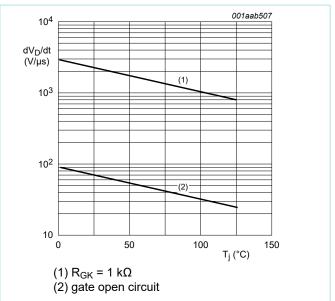


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

# 10. Package outline

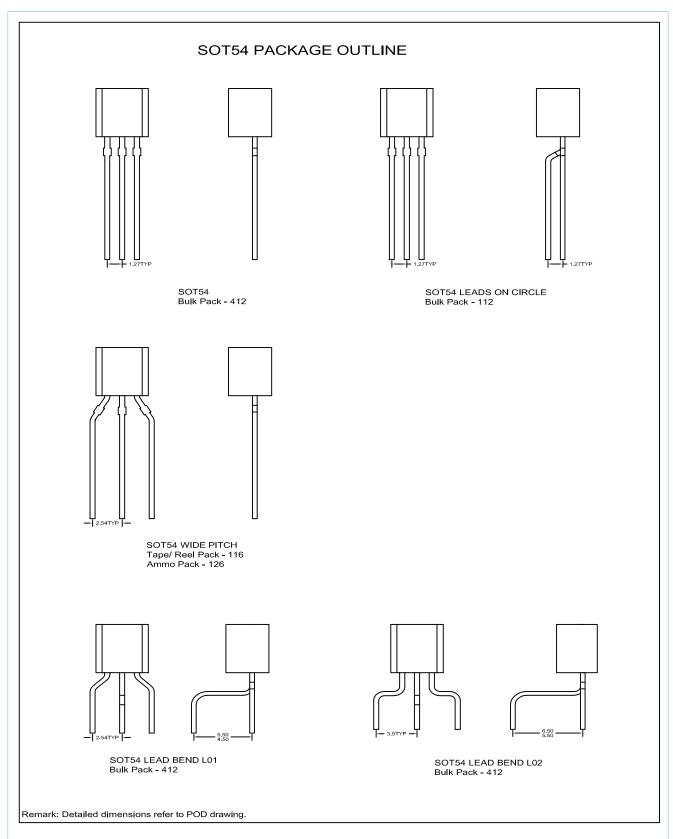


Fig. 13. Package outline TO-92 (SOT54)

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## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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For more information, please visit: http://www.ween-semi.com
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